



MM54HC4002/MM74HC4002

Dual 4-Input NOR Gate

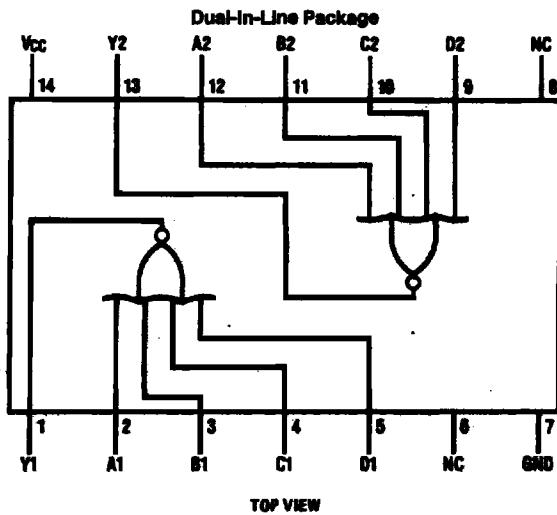
General Description

These NOR gates utilize microCMOS Technology, 3.5 micron silicon gate P-well CMOS, to achieve operating speeds similar to LS-TTL gates with the low power consumption of standard CMOS integrated circuits. All gates have buffered outputs, providing high noise immunity and the ability to drive 10 LS-TTL loads. The 54HC/74HC logic family is functionally as well as pin-out compatible with the standard 54LS/74LS logic family. The 54HC4002/74HC4002 is functionally equivalent and pin-out compatible with the CD4002B. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Typical propagation delay: 8 ns
- Wide power supply range: 2V–6V
- Low quiescent current: 20 μ A maximum (74HC Series)
- Low input current: 1 μ A maximum
- Fanout of 10 LS-TTL loads

Connection Diagram



$$Y = \overline{A + B + C + D}$$

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Order Number **MM54HC4002J** or **MM74HC4002J, N**
 See NS Package J14A or N14A

Absolute Maximum Ratings (Notes 1 & 2)

Supply Voltage (V_{CC})	-0.5 to +7.0V
DC Input Voltage (V_{IN})	-1.5 to V_{CC} +1.5V
DC Output Voltage (V_{OUT})	-0.5 to V_{CC} +0.5V
Clamp Diode Current ($ I_{IK}, I_{OK} $)	± 20 mA
DC Output Current, per pin ($ I_{OUT} $)	± 25 mA
DC V_{CC} or GND Current, per pin ($ I_{CC} $)	± 50 mA
Storage Temperature Range (T_{STG})	-65°C to +150°C
Power Dissipation (P_D) (Note 3)	500 mW
Lead Temp. (T_L) (Soldering 10 seconds)	260°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage ((V_{IN}, V_{OUT}))	0	V_{CC}	V
Operating Temp. Range (T_A)			
MM74HC	-40	+85	°C
MM54HC	-55	+125	°C
Input Rise or Fall Times (t_r, t_f)			
$V_{CC} = 2.0V$		1000	ns
$V_{CC} = 4.5V$		500	ns
$V_{CC} = 6.0V$		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V_{CC}	$T_A = 25^\circ C$		$74HC$	$54HC$	Units
				Typ	Guaranteed Limits			
V_{IH}	Minimum High Level Input Voltage		2.0V		1.5	1.5	1.5	V
			4.5V		3.15	3.15	3.15	
			6.0V		4.2	4.2	4.2	
V_{IL}	Maximum Low Level Input Voltage		2.0V		0.3	0.3	0.3	V
			4.5V		0.9	0.9	0.9	
			6.0V		1.2	1.2	1.2	
V_{OH}	Minimum High Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 20 \mu A$	2.0V	2.0	1.9	1.9	1.9	V
			4.5V	4.5	4.4	4.4	4.4	
		$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 4.0 \text{ mA}$ $ I_{OUT} \leq 5.2 \text{ mA}$	6.0V	6.0	5.9	5.9	5.9	V
			4.5V	4.2	3.98	3.84	3.7	
V_{OL}	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 20 \mu A$	2.0V	0	0.1	0.1	0.1	V
			4.5V	0	0.1	0.1	0.1	
		$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 4 \text{ mA}$ $ I_{OUT} \leq 5.2 \text{ mA}$	6.0V	0	0.1	0.1	0.1	V
			4.5V	0.2	0.26	0.33	0.4	
I_{IN}	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		± 0.1	± 1.0	± 1.0	μA
I_{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	6.0		2.0	20	40	μA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{OH} and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at $V_{CC} = 5.5V$ and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN} , I_{CC} , and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

AC Electrical Characteristics $V_{CC} = 5V$, $T_A = 25^\circ C$, $C_L = 15 \text{ pF}$, $t_r = t_f = 6 \text{ ns}$

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL}, t_{PLH}	Maximum Propagation Delay		11	20	ns

AC Electrical Characteristics $V_{CC} = 2.0V \text{ to } 6.0V$, $C_L = 50 \text{ pF}$, $t_r = t_f = 6 \text{ ns}$

Symbol	Parameter	Conditions	V_{CC}	$T_A = 25^\circ C$		$74HC$	$54HC$	Units
				Typ	Guaranteed Limits			
t_{PHL}, t_{PLH}	Maximum Propagation Delay		2.0V	40	120	151	179	ns
			4.5V	12	24	30	36	
			6.0V	10	20	26	30	
t_{TLH}, t_{THL}	Maximum Output Rise and Fall Time		2.0V	30	75	95	110	ns
			4.5V	10	15	19	22	
			6.0V	9	13	16	18	
C_{PD}	Power Dissipation Capacitance (Note 5)	(per gate)		25				pF
C_{IN}	Maximum Input Capacitance			5	10	10	10	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.